



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: Mitsuhiro Nakamura et al.

Atty. Docket No. 075834.00079

Serial No.: 09/ 862,894

Group Art Unit: 2836

Filed: May 22, 2001

Examiner: Isabel Rodriguez

Invention: "PROTECTION CIRCUIT OF FIELD EFFECT TRANSISTOR
AND SEMICONDUCTOR DEVICE"

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DEVANS
5-16-03

AMENDMENT A

Assistant Commissioner of Patents
Washington, D.C. 20231

S I R:

In response to the Office Action dated February 7, 2003, please amend the application
as follows:

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IN THE CLAIMS:

1. (Once Amended) A protection circuit of a field effect transistor for protecting a
gate electrode of the field effect transistor against surge breakdown, comprising:

a diode array ~~in which~~ having a plurality of forward direction first diodes and reverse
direction second diodes, the number of ~~which is~~ second diodes being equal to that of the first
diodes, are cascade-connected,

wherein a gate electrode of the field effect transistor is grounded through the diode
array.

2. (Once Amended) A protection circuit of a field effect transistor according to claim
1, wherein ~~the~~ each diode of the diode array is formed as a Schottky barrier diode made of an
n+-type layer having a high doping concentration and a Schottky electrode provided on the

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